

Silicon NPN Power Transistors

2SD1403

DESCRIPTION

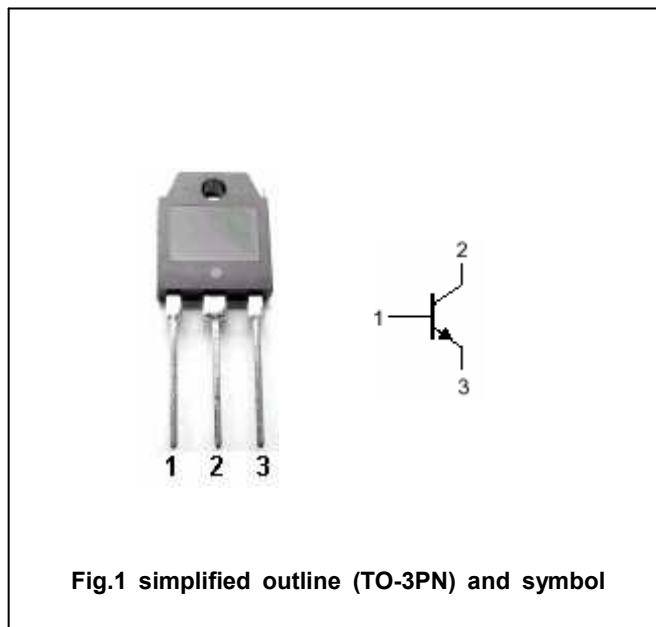
- With TO-3PN package
- High speed switching
- High voltage,high reliability
- Wide area of safe operation

APPLICATIONS

- For CRT horizontal output applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------|-----------------------------|------------------------|---------|------------------|
| V_{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V_{CEO} | Collector-emitter voltage | Open base | 800 | V |
| V_{EBO} | Emitter-base voltage | Open collector | 6 | V |
| I_C | Collector current | | 6 | A |
| P_C | Collector power dissipation | $T_C=25^\circ\text{C}$ | 120 | W |
| T_j | Junction temperature | | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | | -55~150 | $^\circ\text{C}$ |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =100mA; I _B =0 | 800 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =1mA; I _C =0 | 6 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =5A; I _B =1A | | | 5.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =5A; I _B =1A | | | 1.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =800V; I _E =0 | | | 10 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =4V; I _C =0 | | | 10 | μA |
| h _{FE} | DC current gain | I _C =1A; V _{CE} =5V | 8 | | | |
| f _T | Transition frequency | I _C =1A; V _{CE} =10V | | 3 | | MHz |

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.